

Arie Ruzin

List of Publications by Year in descending order

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45
papers

506
citations

759055

12
h-index

713332

21
g-index

45
all docs

45
docs citations

45
times ranked

343
citing authors

#	ARTICLE	IF	CITATIONS
1	Study of the charge collection efficiency of CdZnTe radiation detectors. Journal of Electronic Materials, 1996, 25, 1221-1231.	1.0	70
2	Methodology for evaluation of mobility-lifetime product by spectroscopy measurements in CdZnTe spectrometers. Journal of Applied Physics, 1997, 82, 4166-4171.	1.1	55
3	Study of contacts to CdZnTe radiation detectors. Journal of Electronic Materials, 1997, 26, 756-764.	1.0	48
4	Statistical models for charge collection efficiency and variance in semiconductor spectrometers. Journal of Applied Physics, 1997, 82, 2754-2758.	1.1	30
5	Monolithic coupling of a SU8 waveguide to a silicon photodiode. Journal of Applied Physics, 2003, 94, 7932.	1.1	24
6	Special issue on selected papers from EMRS: Carrier transport, photonics and sensing. Journal of Materials Science: Materials in Electronics, 2020, 31, 1-1.	1.1	24
7	Passivation and surface leakage in CdZnTe spectrometers. Applied Physics Letters, 1997, 71, 2214-2215.	1.5	20
8	A model for the growth of cdte by metal organic chemical vapor deposition. Journal of Electronic Materials, 1991, 20, 609-613.	1.0	17
9	Comment on Cd _{1-x} Zn _x Te Schottky rectifiers. Applied Physics Letters, 1997, 71, 2214-2215.	0.7	13
10	Atomic Structure and Electrical Properties of In(Te) Nanocontacts on CdZnTe(110) by Scanning Probe Microscopy. Advanced Functional Materials, 2010, 20, 215-223.	7.8	12
11	Effect of Electron Injection on Minority Carrier Transport in 10 MeV Proton Irradiated $\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2020, 9, 045018.	0.9	12
12	Variable temperature probing of minority carrier transport and optical properties in $\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$. APL Materials, 2022, 10, .	2.2	12
13	UV photon assisted control of interface charge between CdTe substrates and metalorganic chemical vapor deposition CdTe epilayers. Journal of Electronic Materials, 1993, 22, 977-983.	1.0	11
14	Dark noise currents and energy resolution of CdZnTe spectrometers. Journal of Electronic Materials, 1998, 27, 800-806.	1.0	11
15	Simulation of Schottky and Ohmic contacts on CdTe. Journal of Applied Physics, 2011, 109, .	1.1	11
16	Electron beam probing of non-equilibrium carrier dynamics in 18 MeV alpha particle- and 10 MeV proton-irradiated Si-doped $\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$ Schottky rectifiers. Applied Physics Letters, 2021, 118, .	1.5	10
17	Characterization of dark noise in CdZnTe spectrometers. Journal of Electronic Materials, 1998, 27, 807-812.	1.0	9
18	Temperature dependence of cathodoluminescence emission in irradiated Si-doped $\text{In}^{2+}\text{-Ga}_{2}\text{O}_{3}$. AIP Advances, 2021, 11, .	0.6	9

#	ARTICLE	IF	CITATIONS
19	Impact of radiation and electron trapping on minority carrier transport in $\text{i}^{\text{n}}\text{p}^{\text{n}}$ -Ga ₂ O ₃ . Applied Physics Letters, 2022, 120, .	1.5	9
20	Study of bulk grown silicon-germanium radiation detectors. Journal of Applied Physics, 2004, 95, 5081-5087.	1.1	8
21	Anomalous behavior of epitaxial indium nano-contacts on cadmium-zinc-telluride. Applied Physics Letters, 2012, 101, 132108.	1.5	7
22	Impact of polishing on crystallinity and static performance of Cd _{1-x} Zn _x Te. Applied Physics Letters, 2012, 101, 132108.	0.7	7
23	Impact of electron injection on carrier transport and recombination in unintentionally doped GaN. Journal of Applied Physics, 2020, 128, .	1.1	7
24	Simulation of metal-semiconductor-metal devices on heavily compensated Cd _{0.9} Zn _{0.1} Te. Journal of Applied Physics, 2012, 112, 104501.	1.1	6
25	Effects of surface treatment on static characteristics of In/Cd _{1-x} Zn _x Te. Applied Physics Letters, 2012, 101, 132108.	0.7	6
26	Simulating Downscaling of Ohmic Contacts on Wide-Bandgap Low-Resistivity Semiconductors. IEEE Transactions on Electron Devices, 2012, 59, 1668-1671.	1.6	5
27	Simulation of compensated and overcompensated Cd _{1-x} Zn _x Te. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2013, 718, 361-362.	0.7	5
28	Scaling effects in ohmic contacts on semiconductors. Journal of Applied Physics, 2015, 117, 164502.	1.1	5
29	Impact of surface treatments on I - V characteristics in Cd _{1-x} Zn _x Te and Cd _{1-x} Mn _x Te crystals. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2012, 705, 103-107.	0.7	5
30	Study of material uniformity in high-resistivity Cd _{1-x} Zn _x Te. Applied Physics Letters, 2012, 101, 132108.	0.7	5
31	Photon assisted reduction of interface charge between CdTe substrates and metalorganic chemical vapor deposition CdTe epilayers. Journal of Applied Physics, 1993, 73, 995-997.	1.1	4
32	Performance study of CdZnTe spectrometers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 409, 232-235.	0.7	4
33	Scaling effects in Schottky contacts. Journal of Applied Physics, 2015, 118, 204502.	1.1	4
34	Edge effect in ohmic contacts on high-resistivity semiconductors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2016, 806, 356-359.	0.7	4
35	High quality planar Cd _{1-x} Mn _x Te room-temperature radiation detectors. Applied Physics Letters, 2021, 119, 062103.	1.5	3
36	Photon assisted growth of HgTe by metalorganic chemical vapor deposition. Journal of Electronic Materials, 1993, 22, 281-288.	1.0	2

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37	Self-assembled formation and transformation of In/CdZnTe(110) nano-rings into camel-humps. Applied Physics Letters, 2012, 100, 213116.	1.5	2
38	On Polarization of Compensated Detectors. IEEE Transactions on Nuclear Science, 2016, 63, 1188-1193.	1.2	2
39	CVD diamond metallization and characterization. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2017, 845, 76-79.	0.7	2
40	Printed silver contacts to CVD diamond detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 927, 349-352.	0.7	2
41	Novel X- and gamma-ray sensors based on bulk-grown silicon-germanium. IEEE Transactions on Electron Devices, 2003, 50, 2581-2583.	1.6	1
42	Subthreshold slope and transconductance degradation model in cycled hot electron injection programmed/hot hole erased silicon-oxide-nitride-oxide-silicon memories. Journal of Applied Physics, 2008, 104, 054502.	1.1	1
43	Study of insulator traps in InSb InSb/SiO _x /Metal devices. Journal of Applied Physics, 2010, 107, 084510.	1.1	1
44	Printed silver contacts for Cd _{1-x} Zn _x Te radiation detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 927, 349-352.	0.7	1
45	STUDY OF LITHIUM DIFFUSION INTO SILICON-GERMANIUM CRYSTALS. , 2008, , .		0